





ST's power discrete solutions improve performance and density in new energy vehicles

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SiC MOSFET technology & product roadmap





Silicon carbide MOSFET technology executive strategy

Technology Roadmap **Product Status** 2014: Gen1 Continuous scale-down • 1200 V (0 to 300 kHz) Gen1 [Ron x area] In full production • 1700 V (0 to 300 kHz) • 20 V driving voltage 2018: Gen2 x2 shrinkage • 650 V (0 to 500 kHz) Gen2 In full production • 1200 V (0 to 500 kHz) Planar Planar • 18 V driving voltage 2020: Gen3 x4 shrinkage • 750 V (0 to 500 kHz) **Technology qualified in Q4 2020** 3rd Gen • 1200 V (0 to 500 kHz) 18 V* driving voltage 2023: Gen4 In development x5 shrinkage 4th Gen • **750 V** (0 to 1 MHz) Expected introduction in 2023 • 1200 V (0 to 1 MHz) 15 V* driving voltage Planar 2025: Gen 5 Feasibility and simulation results in 2022 **Radical innovation** 5th Gen



^{*} Suggested for best performance

STPOWER SiC MOSFET positioning vs. product family & package





HV MOSFET technology & product roadmap



High-voltage power MOSFET for automotive

Technology roadmap

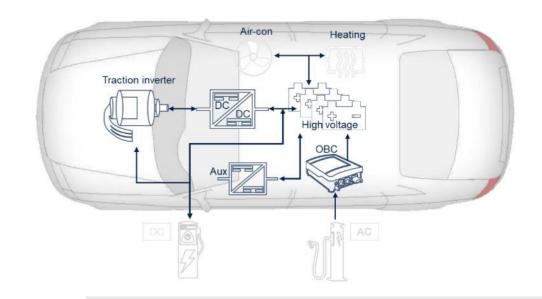


Advanced packaging









OBC
DC-DC Converter

MDmesh DM2, DM6, DM9* (SOP Q4'23)

Battery Management System MDmesh DM6, MDmesh K5 MDmesh K6* (SOP Q1'24)

Aux for Traction inverter

MDmesh K5



High-voltage silicon MOSFET M9 – the next step forward

The most complete product portfolio for high power and efficiency systems



- Best R_{DS(on)} x area
- Step forward for both hard and soft switching
- DM9 FAST diode embedded version available
- Wider product portfolio

Why choose M9/DM9?

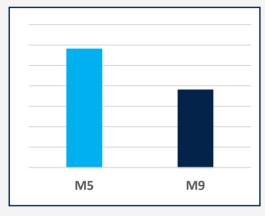
- Only one technology for hard (PFC) and soft switching (LLC)
- Higher power level and better efficiency maintaining same package
- Increasing power density providing smaller package
- Improved system ruggedness applying new production processes
- Better electrical parameters, giving more safety to the system



MDmesh M9 / DM9 main features

R_{ds(ON)}

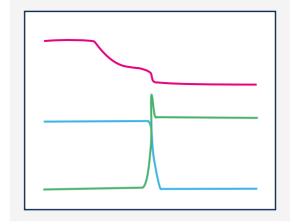
- Very low R_{ds(ON)} per area
- Suitable for Hard switching topologies
- Best choice for Resonant high power density system



Power losses



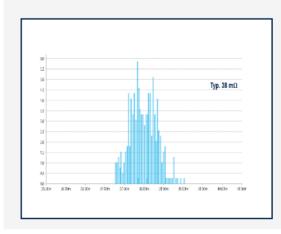
- Reducing switching energy losses
- · Reducing switching time
- Increasing switching frequency



Process



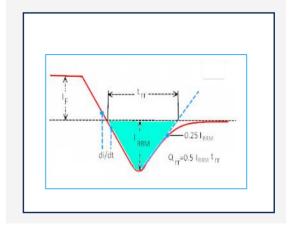
- Reduced BVdss spread <70V
- Reduced Vth spread <1V
- Ruggedness (UIS test)



Robustness



- · Static dv/dt up to 120V/ns
- Dynamic dv/dt up to 50V/ns (M9)
- Dynamic dv/dt up to 120V/ns (DM9)





Rectifier technology & product roadmap



Leadership in power management DFD* rectifier footprint in multiple markets



High-voltage diodes



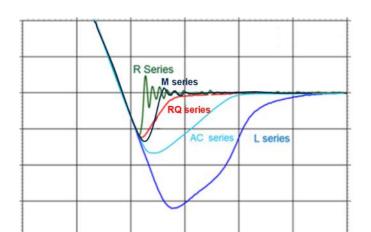
SiC diodes



Low-voltage diodes

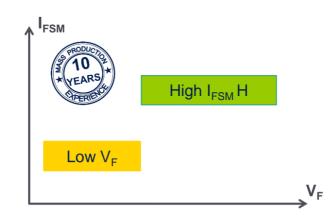
> 200V

STTH series
STBR series



650V & 1200V

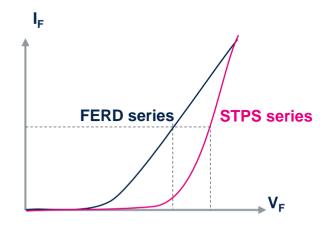
STPSC series



✓ AEC-Q101 = Y suffix in part numbers✓ PPAP capable



FERD series
STPST series



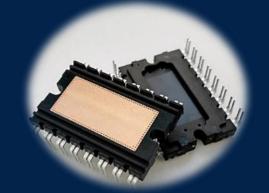


Power module solution

ACEPACK DRIVE



ACEPACK DMT-32



ACEPACK 1 & 2







Dual in line, molded, through-hole 32-pin power modules

Power module segmentation and strategy



Market Segment



Key factors for growth



Products

H(EV) & Ecosystem: Traction



- Car electrification mega-trend due to CO₂ worldwide reduction programs
- Maximize production capacity of ACEPACK DRIVE SiC MOSFET: the "commodity" power module solution adopted by majority of car makers for the current and next Platform.
- ACEPACK DRIVE SiC MOSFET & IGBT+Diode
- Customized Transfer Molded Modules (TMM) for + 2026 platforms Full SiC, IGBT + Diode & Hybrid
- Complete Power Box with advanced technique for interconnection to the cooler

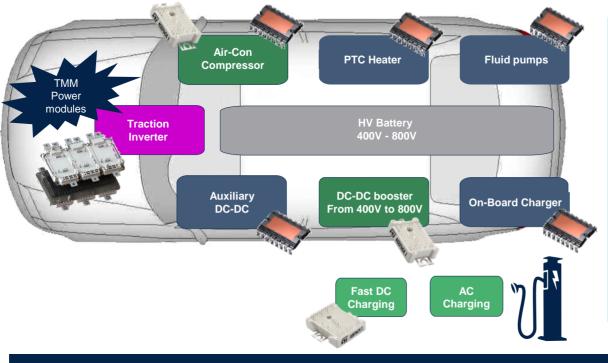
H(EV) & Ecosystem: OBC & Other mechatronic platforms



- Car electrification market is expanding
- Use of new high efficiency topologies/solutions for an increasing miniaturization of the system
- Not only light EV but also truck, van and fuel cell vehicles requiring higher power
- Bi-directionality is requested
- ACEPACK DMT-32: compact and slim power module tailored for car OBC, DC-DC and auxiliaries: 650V/1200V SiC MOSFET based
- ACEPACK 1 & 2: to enabling DC-DC and auxiliary systems for higher power like for truck, van and fuel cell systems.



Automotive application focus: OBC, DC-DC, and traction inverter



Power modules approach main benefits:

- lower occupation → Increased power density
- Easy of cooling system design
- Improved manufacturability: from IMS to PCB
- Improved stray inductance and parasitic components

Applications

















ACEPACK* power module package options

ACEPACK options

ACFPACK 1 3kW to 15kW

ACFPACK 2 10kW to 30kW





Package design

Key features

- Silicon 100% produced and controlled by ST (SiC MOSFET, IGBT, and diodes)
- · Compact design and cost-effective system approach for a plug & play system solution
- Configuration flexibility
- 2500Vrms electrical isolation

Configurations

- CIB
- Six-pack
- Three level boost
- Four-pack
- Half-bridge



Applications



















- Silicon 100% produced and controlled by ST (SiC, MOSFET and diodes)
- Electrically insulated
- Top-side cooling
- Dual-in-line molded through-hole
- 3kVrms electrical isolation

- Four-pack
- Six-pack
- Totem pole





- 750 1200V SiC MOSFET-based switch
- Improved light load performance for extended EV driving ranges
- · Active metal bonding (AMB) substrate for enhanced thermal dissipation
- Different bus bar configuration options
- Extremely low energies dissipation
- Direct cooled Cu baseplate with pin fins





* is a registered and/or unregistered trademark of STMicroelectronics International NV or its affiliates in the EU and/or elsewhere.

ACEPACK 1 and ACEPACK 2 key benefits

Industrial drives, motor control, UPS, automotive EV ecosystems and DC-DC converter



ACEPACK 1 & 2



33.8 x 48 mm



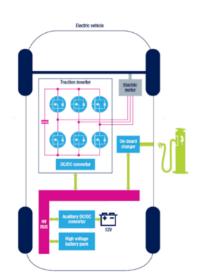
48 x 56.7 mm

- Press fit and solder pin options for configuration flexibility
- Up to 1200V breakdown voltage
- Integrated screw clamps
- All power switches in a module including NTC
- Several current ratings available
- Several configuration options (CIB, six-pack, halfbridge etc..)
- Low stray inductance
- High reliability and robustness, lower power-side board occupation
- Compact design and cost-effective system approach
- Very high-power density



ACEPACK DMT-32 automotive grade power module

DMT-32: Dual in-line Molded Through-hole 32 pin module

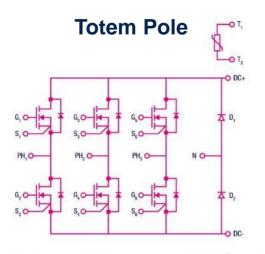


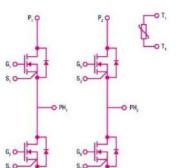
New Power Modules family suitable for OBC, DC-DC and auxiliary applications (*):

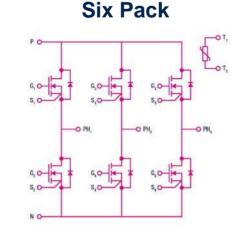
- SiC MOSFET Gen2 and Gen3 power switches used in different configurations: Four pack, Six pack, Totem Pole
- Suitable to cover several sub-function up to 22kW of power range

Four Pack

• SOP: Q4'23(**)

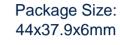














(*) Auxiliary application as: fluid pumps and HVAC and climate control for BEV/HEV; (**) depending on configuration

Direct liquid cooled high-performance power module

Traction inverter for (H)EV, trucks, and buses





Press fit connections for high reliable and long-lasting connection

AQG-324 qualified

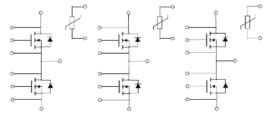
Pin-fin base plate for direct liquid cooling

Dedicated NTC for each single substrate

Best-in-class R_{DS(on)}

ACEPACK DRIVE based on SiC MOSFET Gen 3 1200V & 750V





Internal layout optimized for minimized stray inductance

High reliability and robustness: dice sintered to substrate for SiC-based power modules

Different bus bar available to fit welding or screwing connection methods

AMB substrates for better thermal management for SiC-based power modules

Extremely high-power density

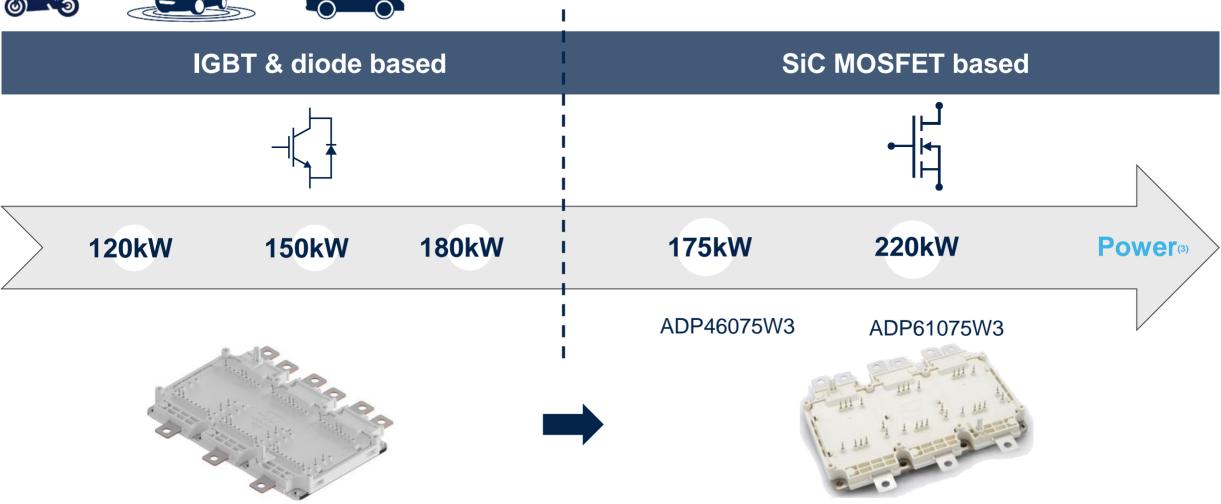


ACEPACK DRIVE for 400V battery





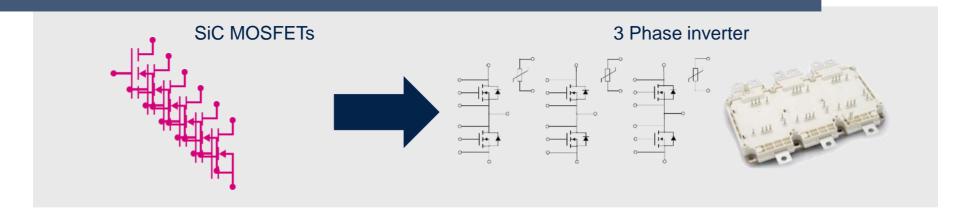






ACEPACK DRIVE for 800V battery

Gen3 SiC MOSFETs: Tailored for high-power traction inverters



 180kW
 230kW
 300kW
 Power

 ADP280120W3
 ADP480120W3





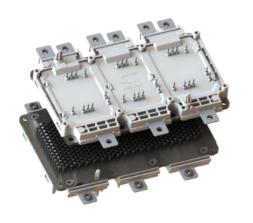






ACEPACK DRIVE SiC-based product portfolio in full production

ACEPACK DRIVE: Full Gen3 SiC MOSFETs



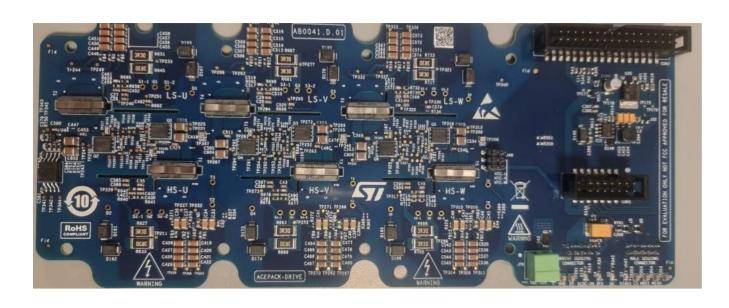
Part number	SiC technology	BV	R _{DS(on)typ} @ 25°C (per switch)	R _{DS(on)typ} @ 175°C (per switch)	Max peak power indication ⁽¹⁾
ADP480120W3(-L)	Gen 3	1200V	1.90 mΩ	$3.35~\text{m}\Omega$	300 kW
ADP360120W3			$2.55~\text{m}\Omega$	$4.25~\text{m}\Omega$	230 kW
ADP280120W3			3.80 mΩ	$6.50~\text{m}\Omega$	180 kW
ADP61075W3(-L)		750V	1.20 mΩ	1.95 mΩ	220 kW
ADP46075W3			1.60 mΩ	2.60 mΩ	175 kW

www.st.com/en/power-modules-and-ipm/acepack-drive/products.html



STEVAL-APD02ACB eval board for SiC-based devices

STEVAL-APD02ACB is fully compatible with ACEPACK DRIVE power press fit pins and requires a dedicated pressing tool to mount it







Proof of Concept available for ACEPACK DRIVE SiC devices only.





New STEVAL with full ASIL/D will be available by end of this year: validation running





Thank you

